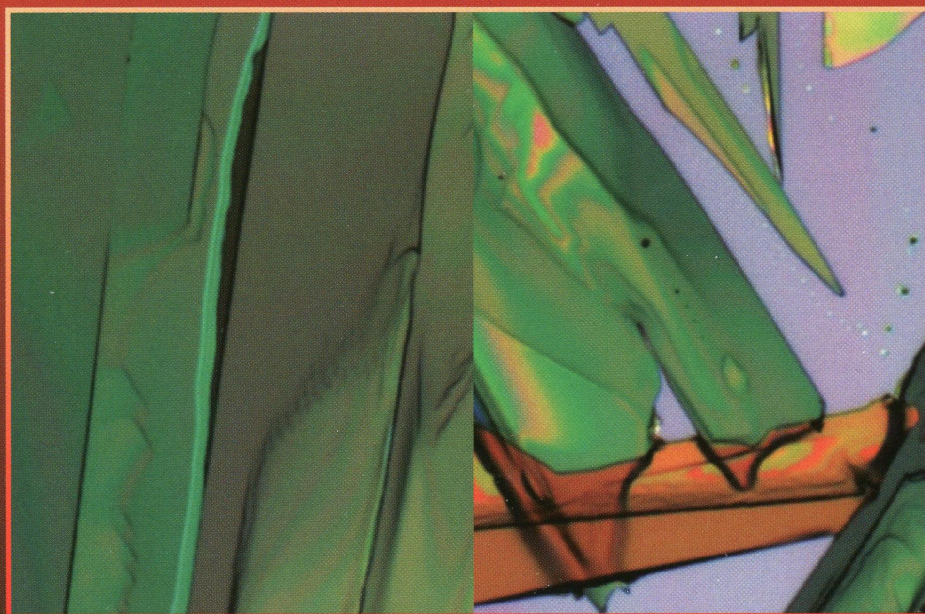


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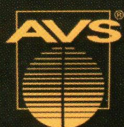
# JVSTB

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## Nanotechnology and Microelectronics: Materials, Processing, Measurement, and Phenomena



*Image credit: Kyeiwaa Asare-Yeboah, Rachel M. Frazier, Greg Szulcowski, and Dawen Li, JVST B 32(5), p. 052401-1*



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## Materials, Processing, Measurement, and Phenomena

Second Series  
Volume 32, Number 5  
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**Erratum: "Semipolar (2021) GaN laser diodes operating at 388 nm grown by plasma-assisted molecular beam epitaxy" [J. Vac. Sci. Technol., B 32, 02C115 (2014)]**

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**Errata: "Role of molybdenum oxide for organic electronics: Surface analytical studies"**  
**[J. Vac. Sci. Technol., B 32, 040801 (2014)]**

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**On The Cover:** *Kyeiwaa Asare-Yeboah, Rachel M. Frazier, Greg Szulczewski, and Dawen Li, JVST B 32(5), p. 052401-1 (2014). Cover shows the enhancement of TIPS pentacene crystalline film resulting from the temperature-gradient technique.*